



FIG. 1
(PRIOR ART)

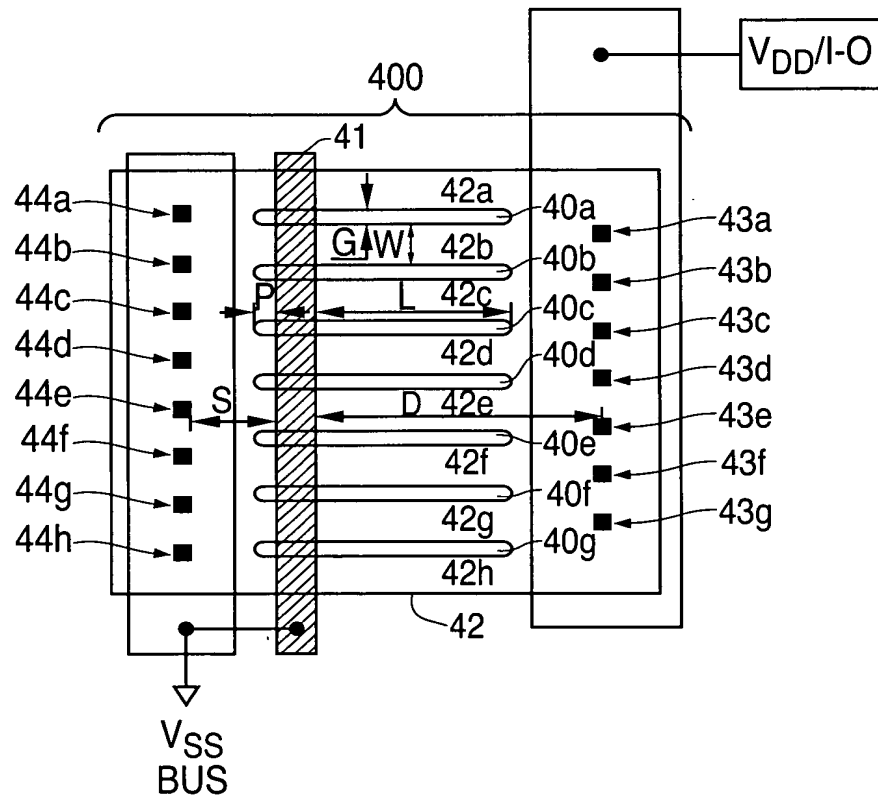


FIG. 2A

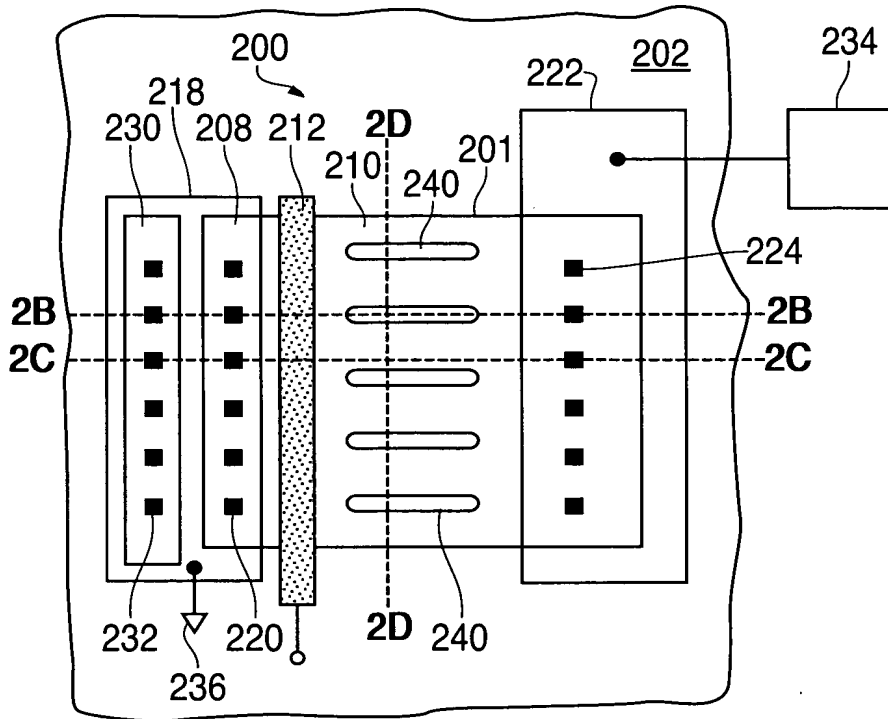
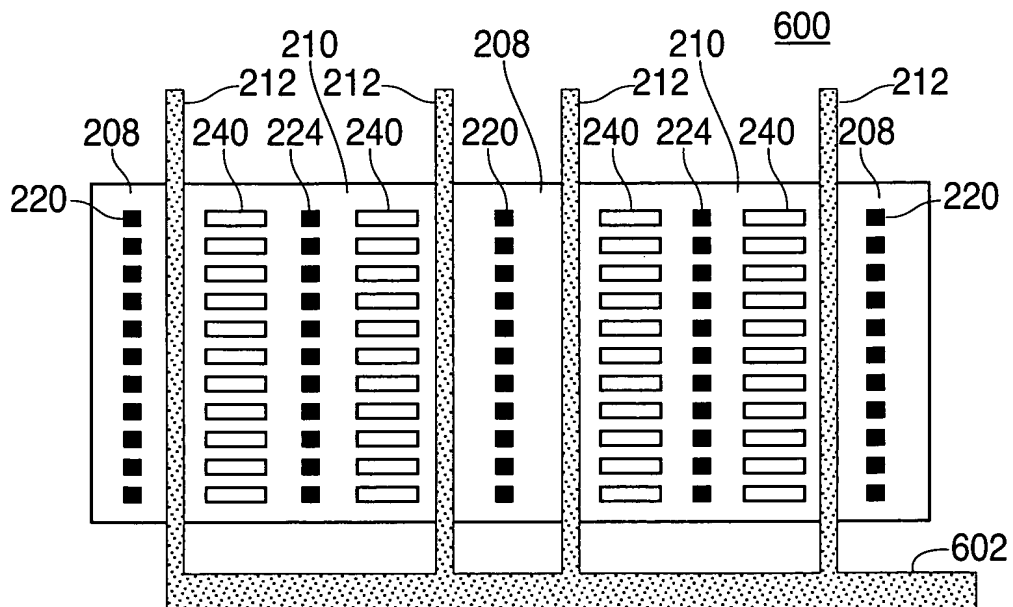


FIG. 6



[illegible]

A cross-sectional view of a semiconductor device 200. The device consists of a substrate 202 with a series of alternating layers 210 and 240. The layers 210 are labeled with "n+" indicating they are n-type semiconductor regions. The layers 240 are unlabeled, representing a different material or doping. The device is capped with a layer 204 at both ends. Contacts 206 are shown at the ends of the device, connected to the substrate 202.

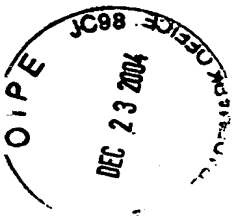


FIG. 3A

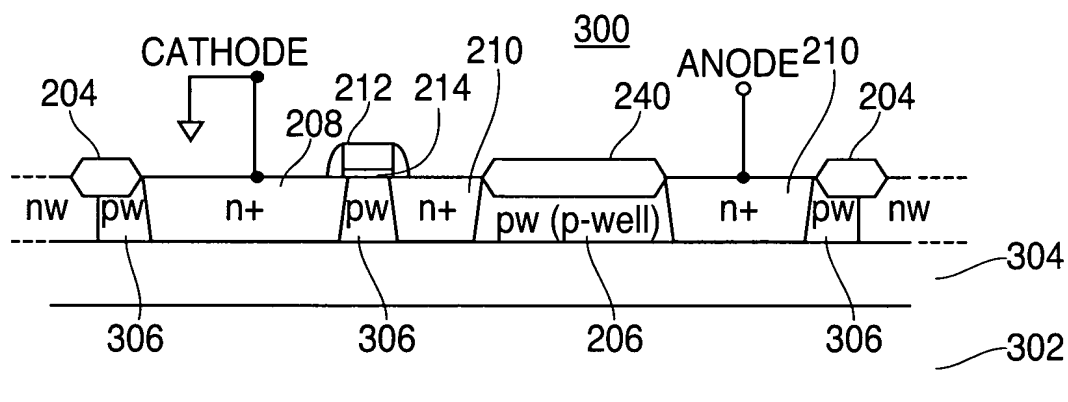


FIG. 3B

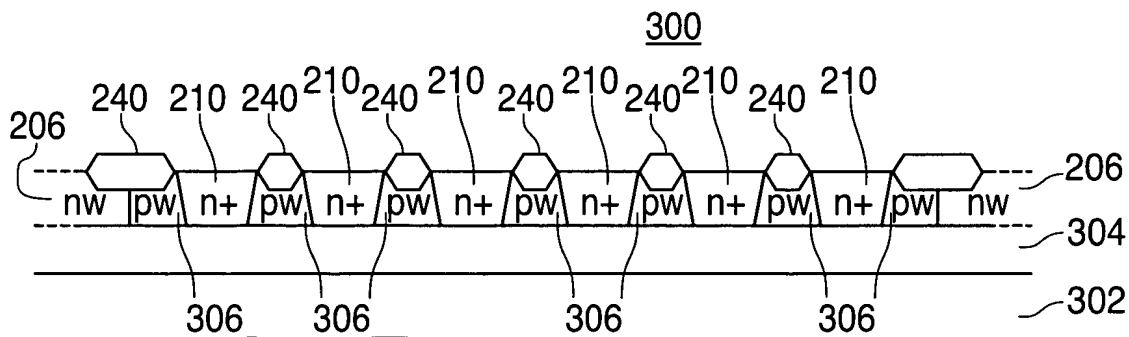




FIG. 4A

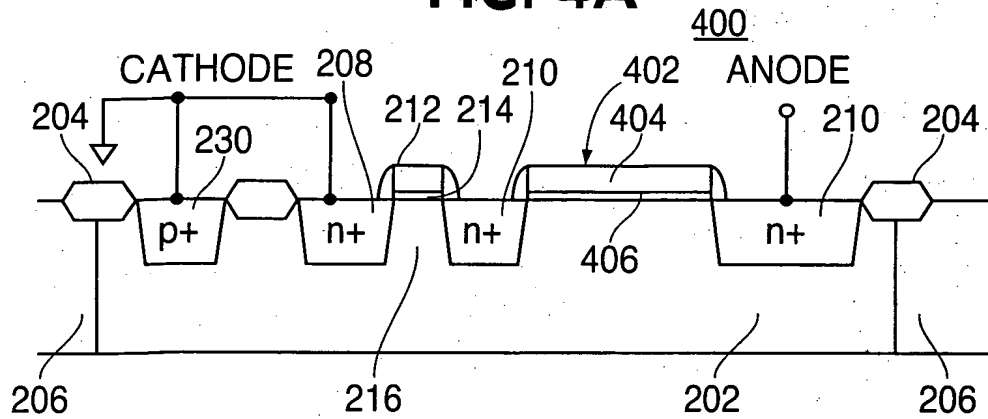


FIG. 4B

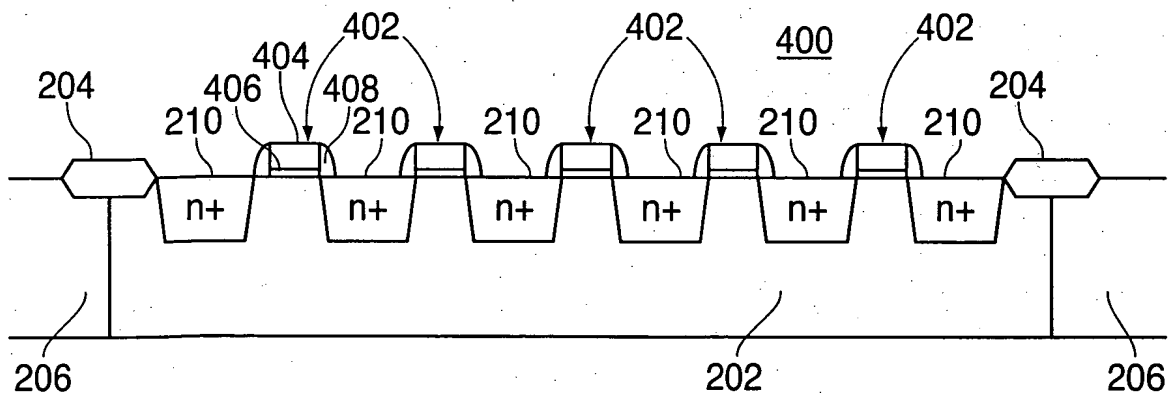
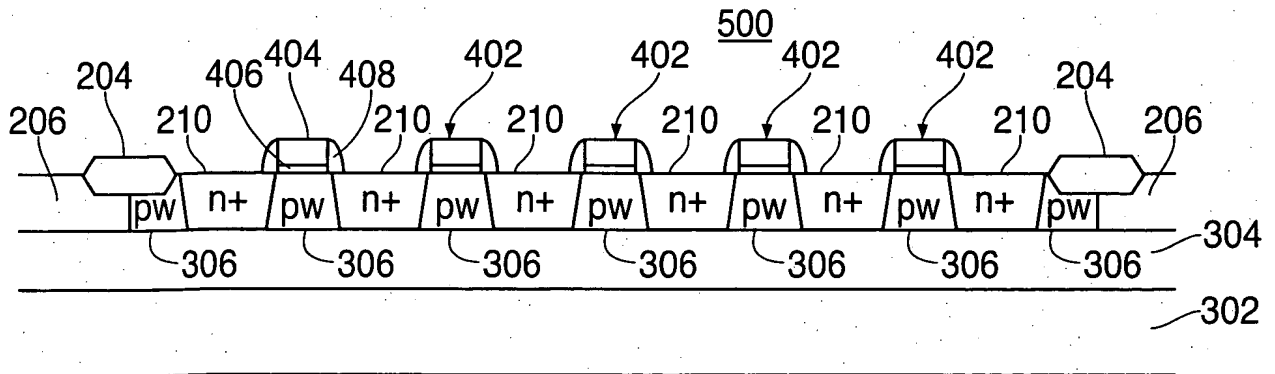


FIG. 5



[illegible][illegible]





FIG. 7A

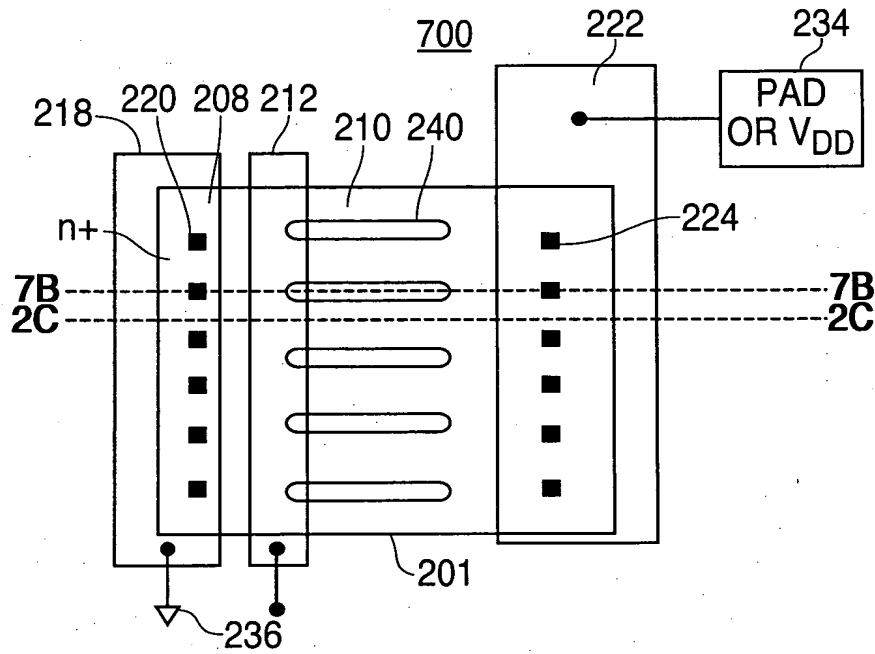


FIG. 7B

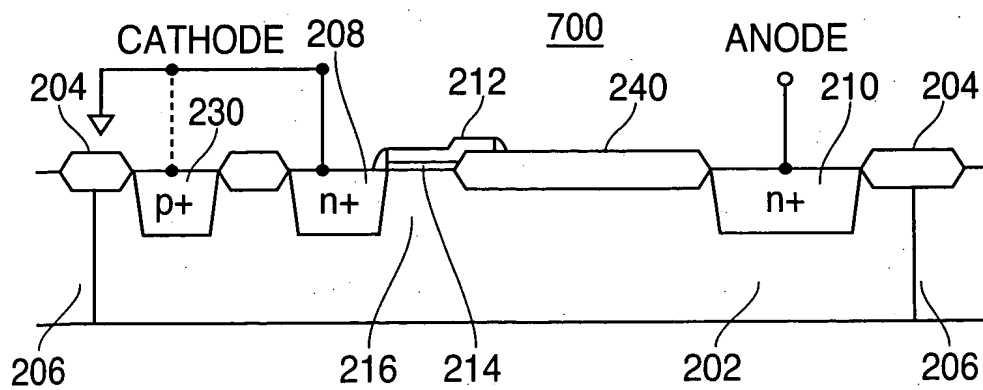


FIG. 7C

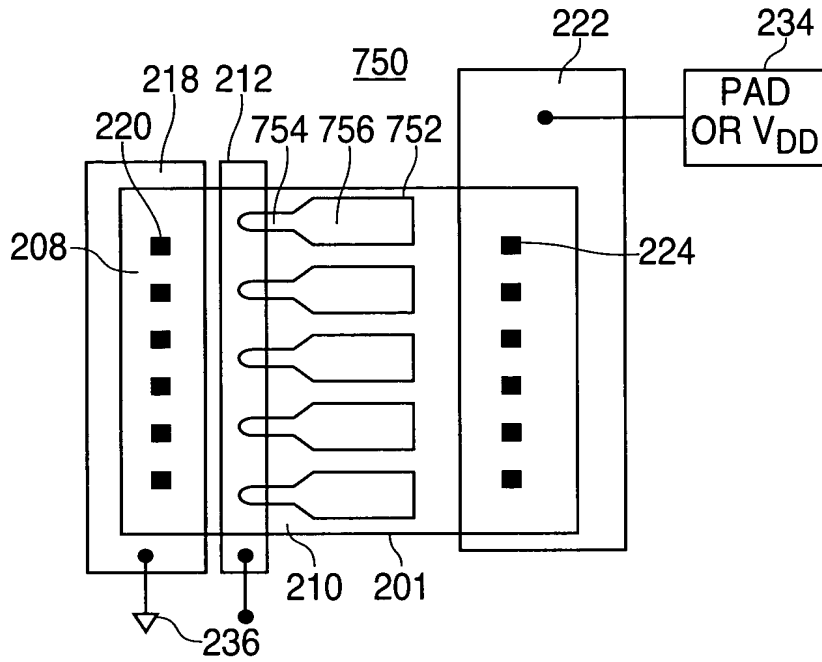
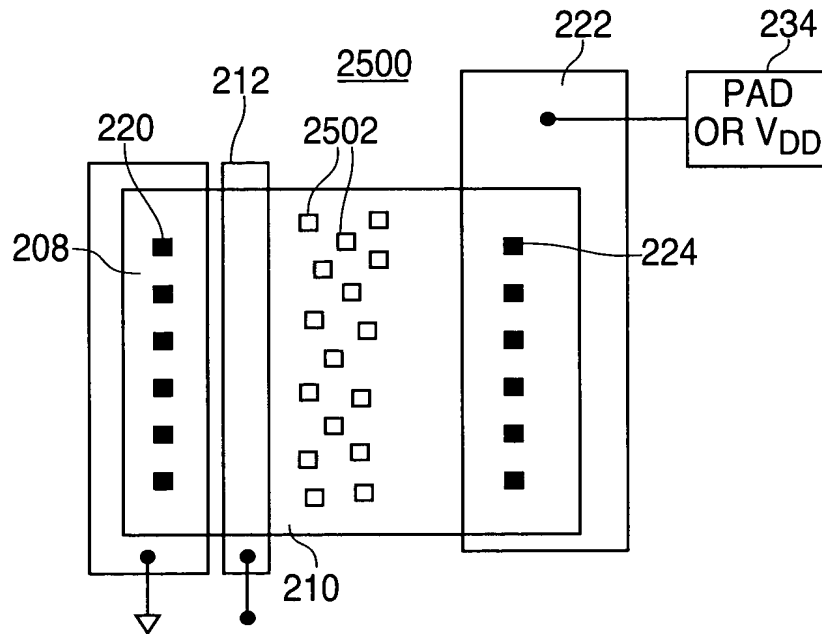


FIG. 25



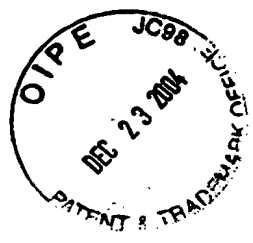


FIG. 8A

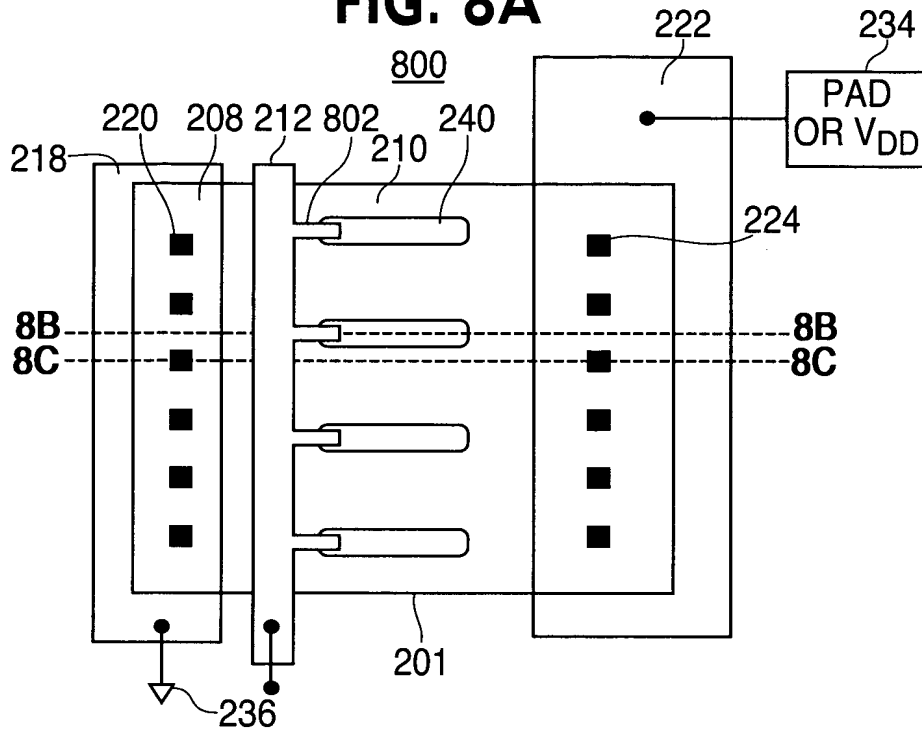


FIG. 8B

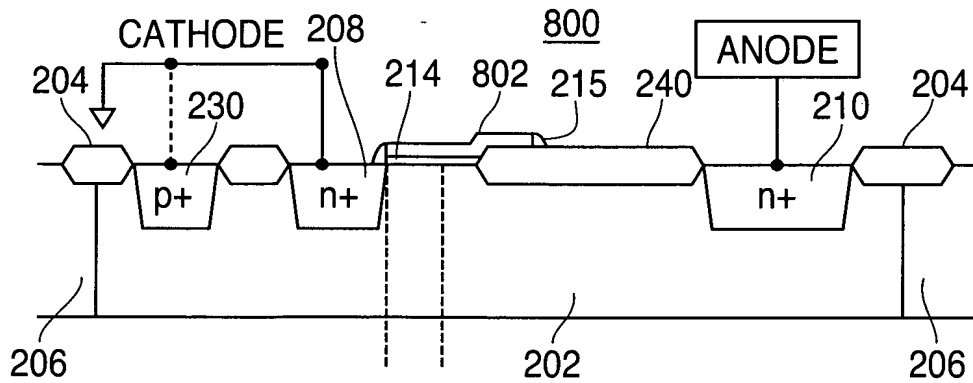


FIG. 8C

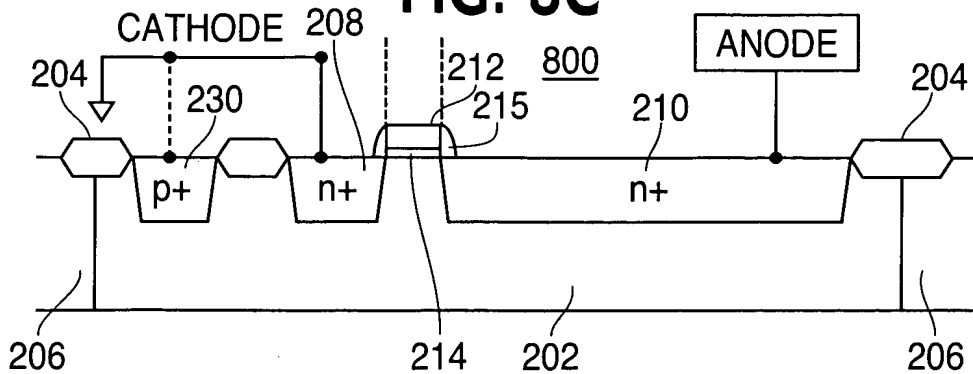




FIG. 9

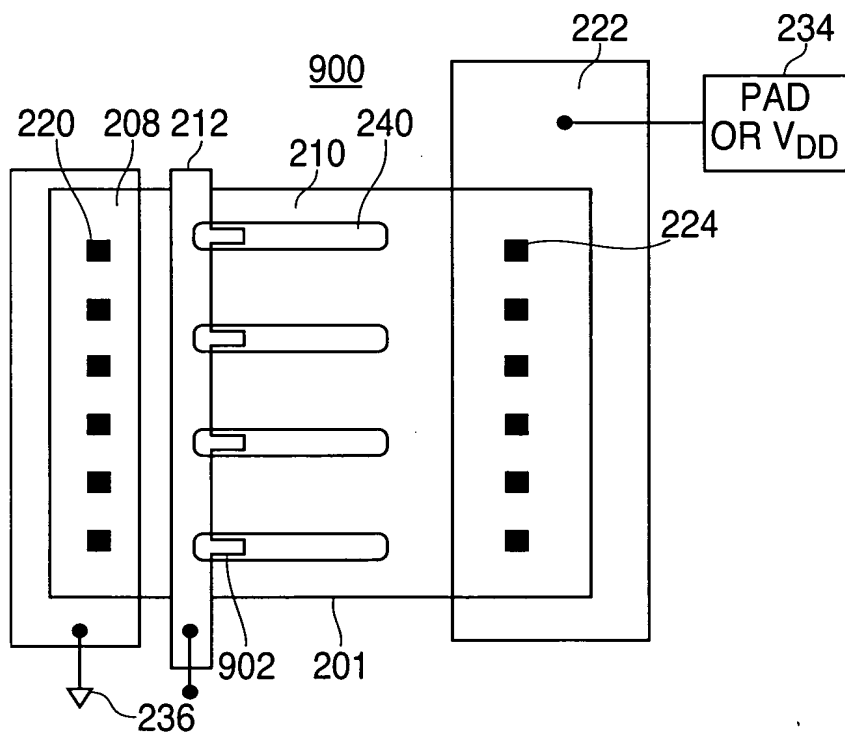




FIG. 10A

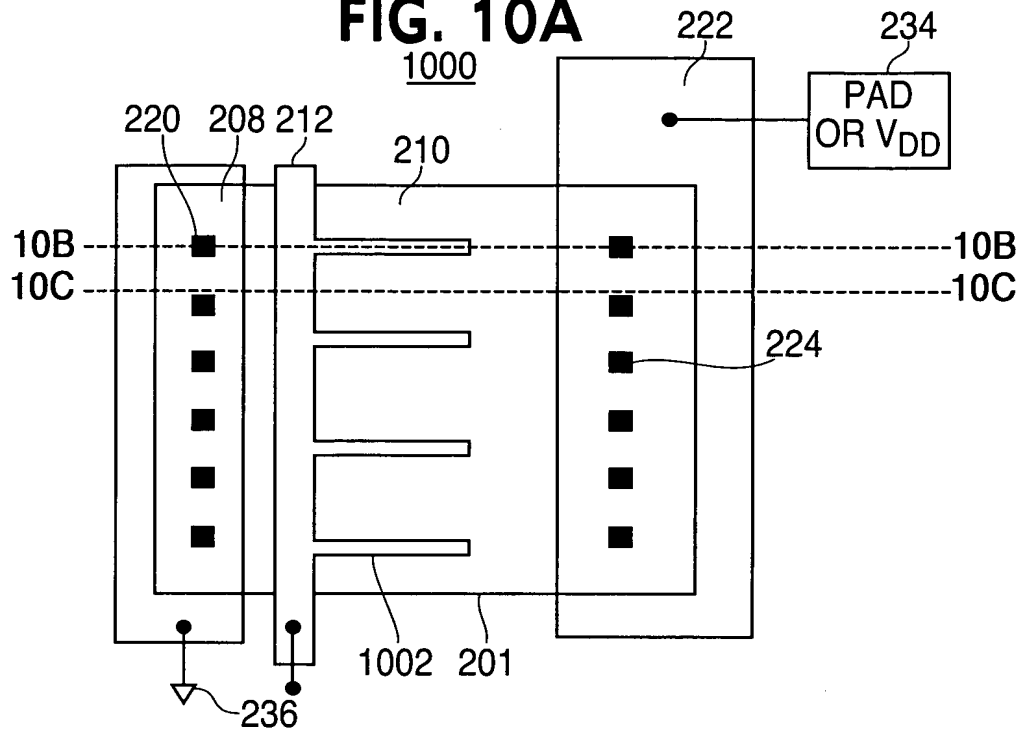


FIG. 10B

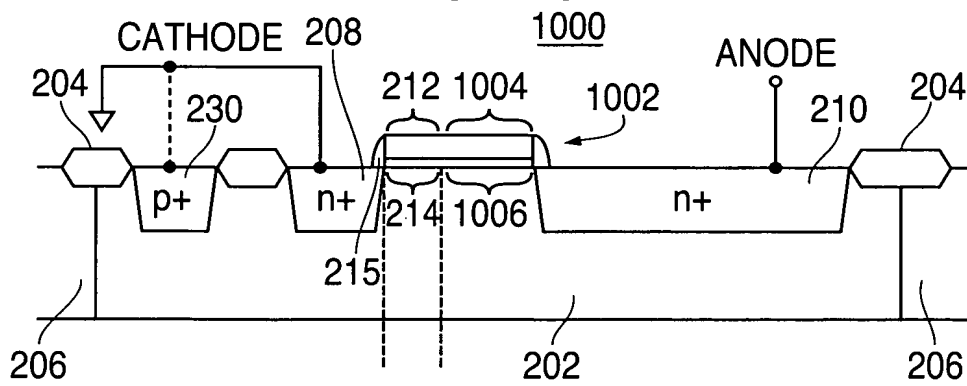


FIG. 10C

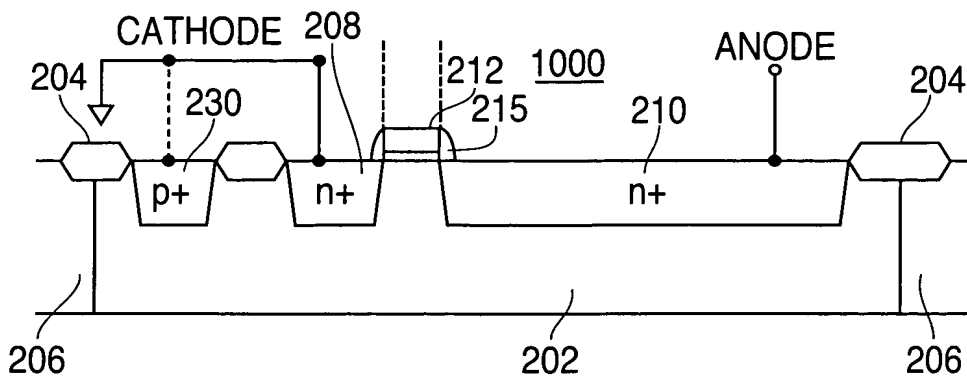




FIG. 11A

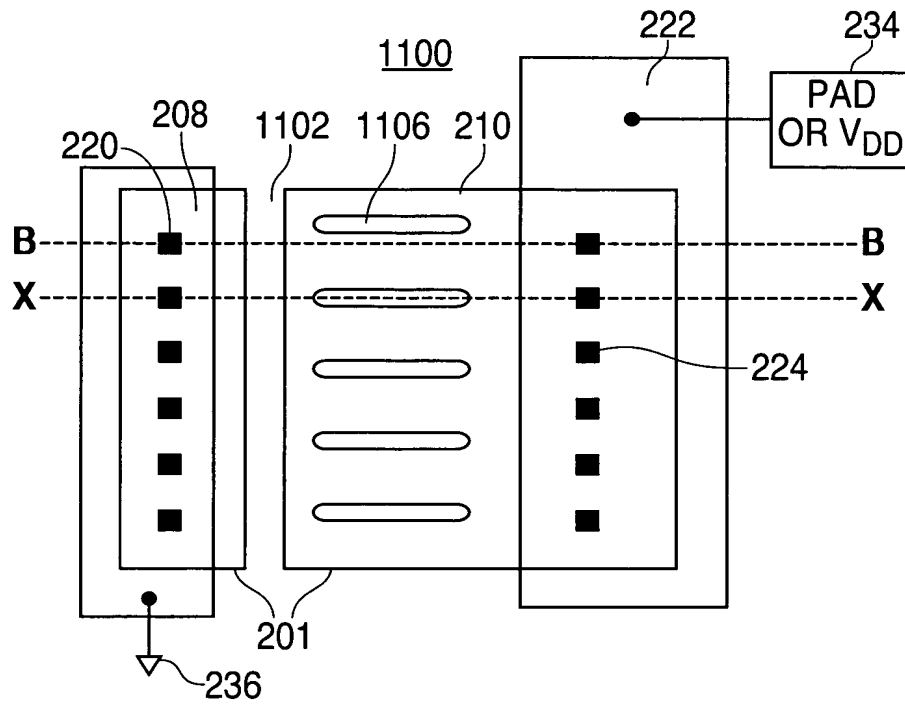
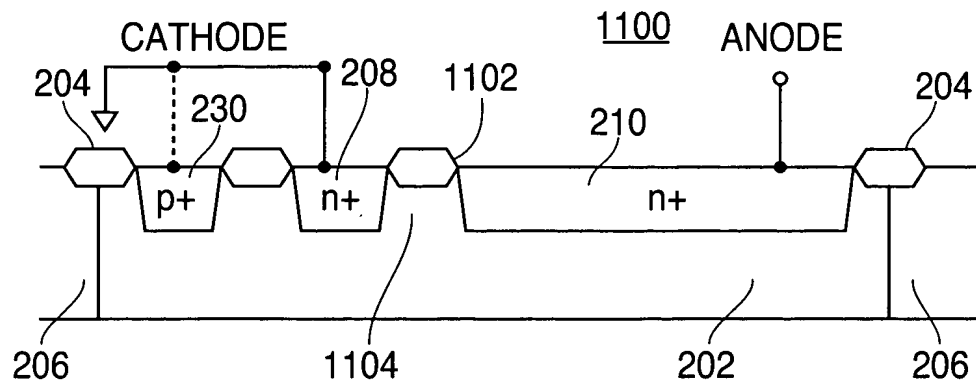


FIG. 11B



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FIG. 11C

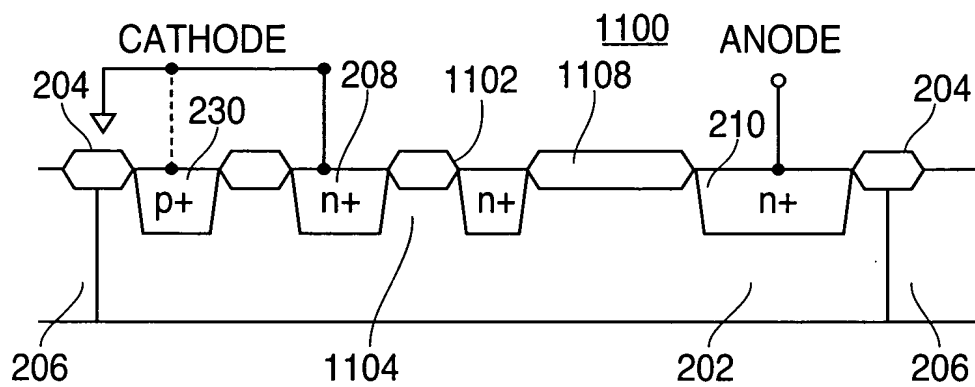
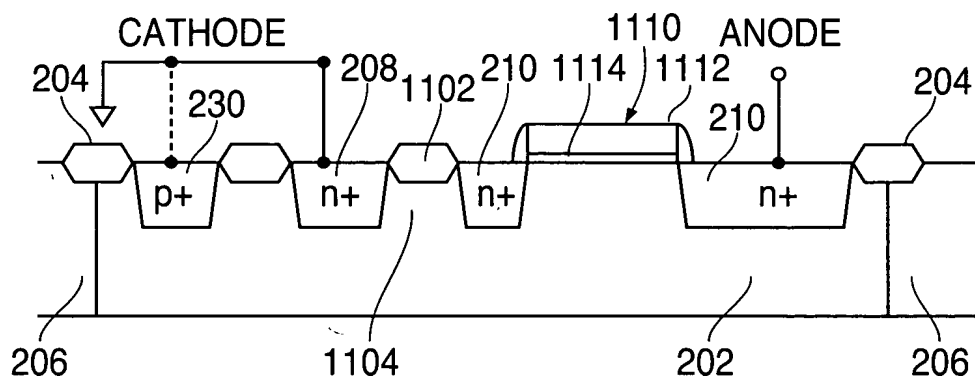


FIG. 11D



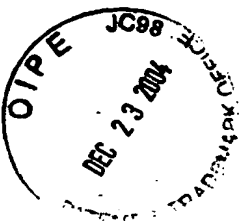


FIG. 12A

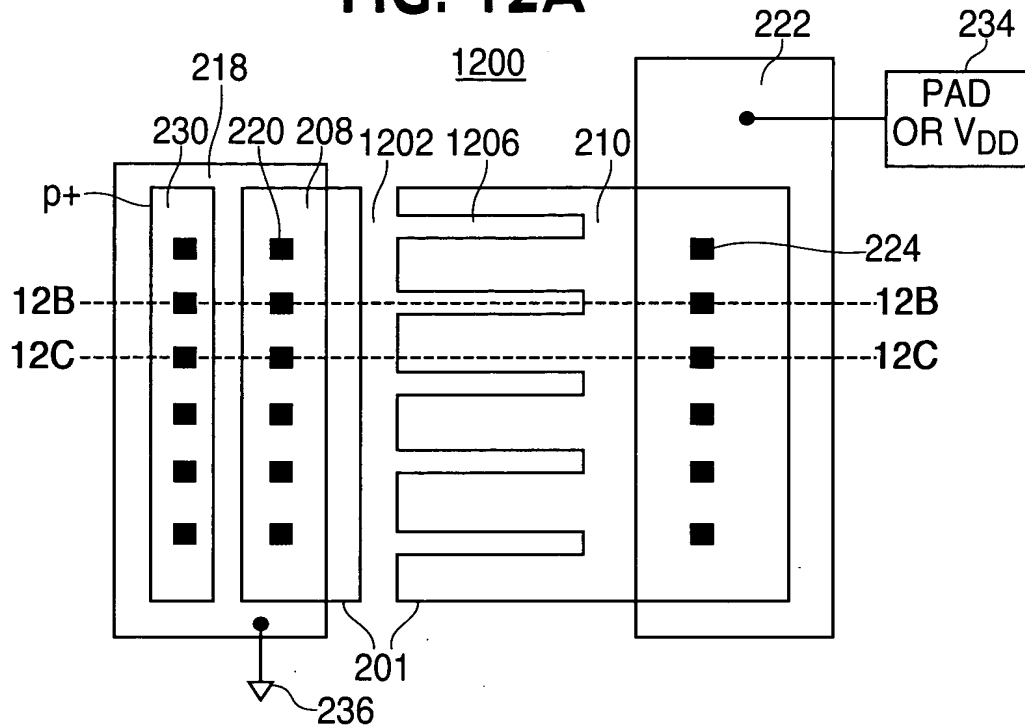


FIG. 12B

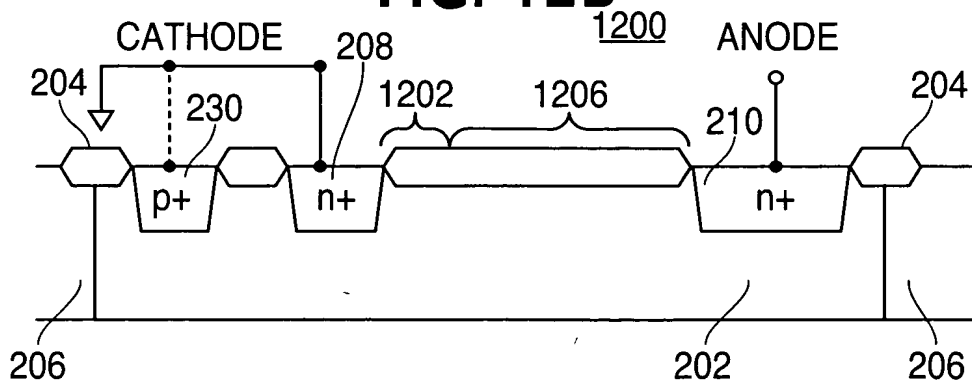


FIG. 12C

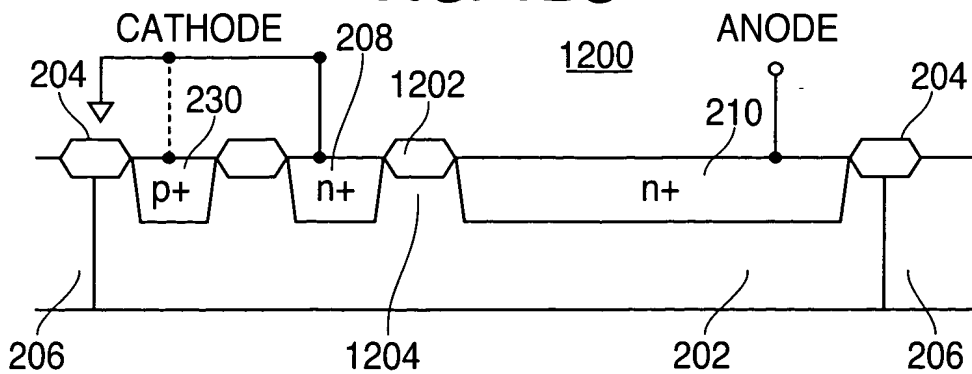


FIG. 13

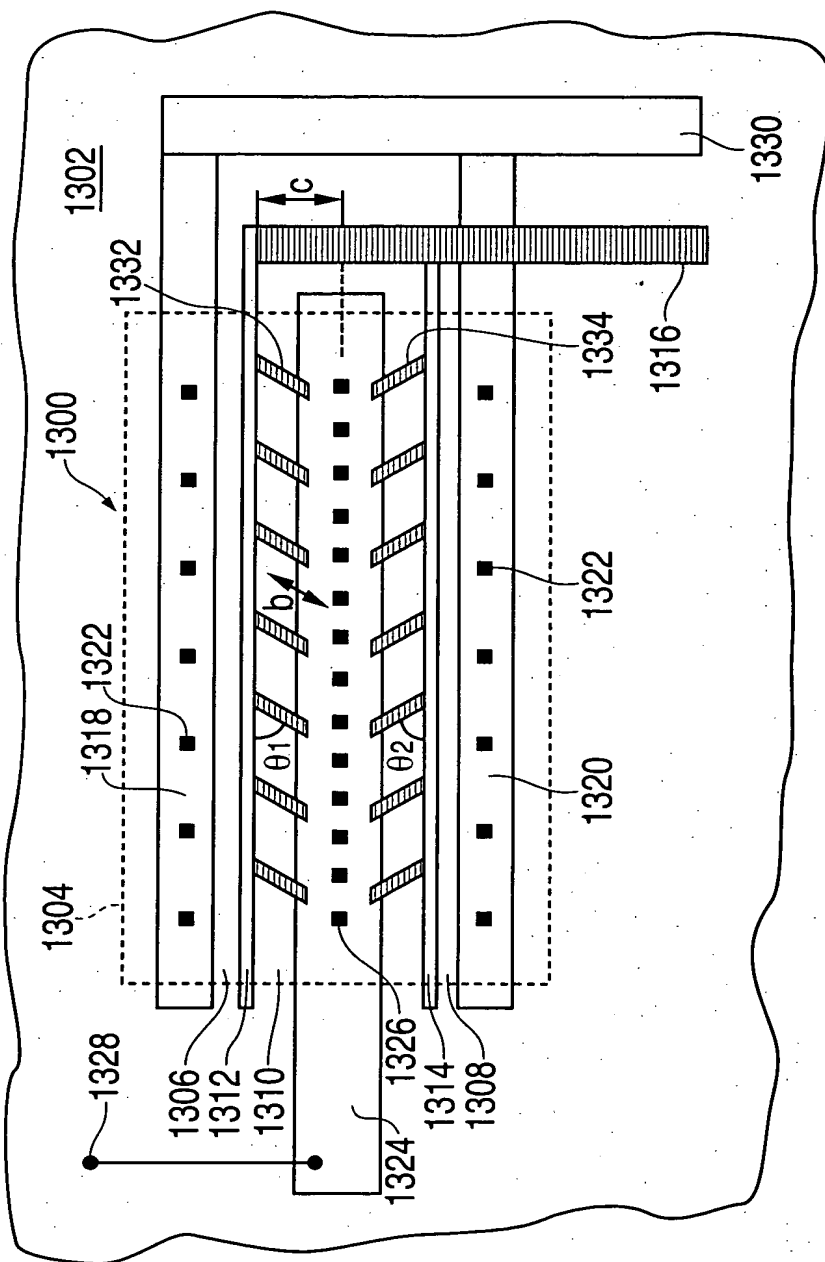


FIG. 14

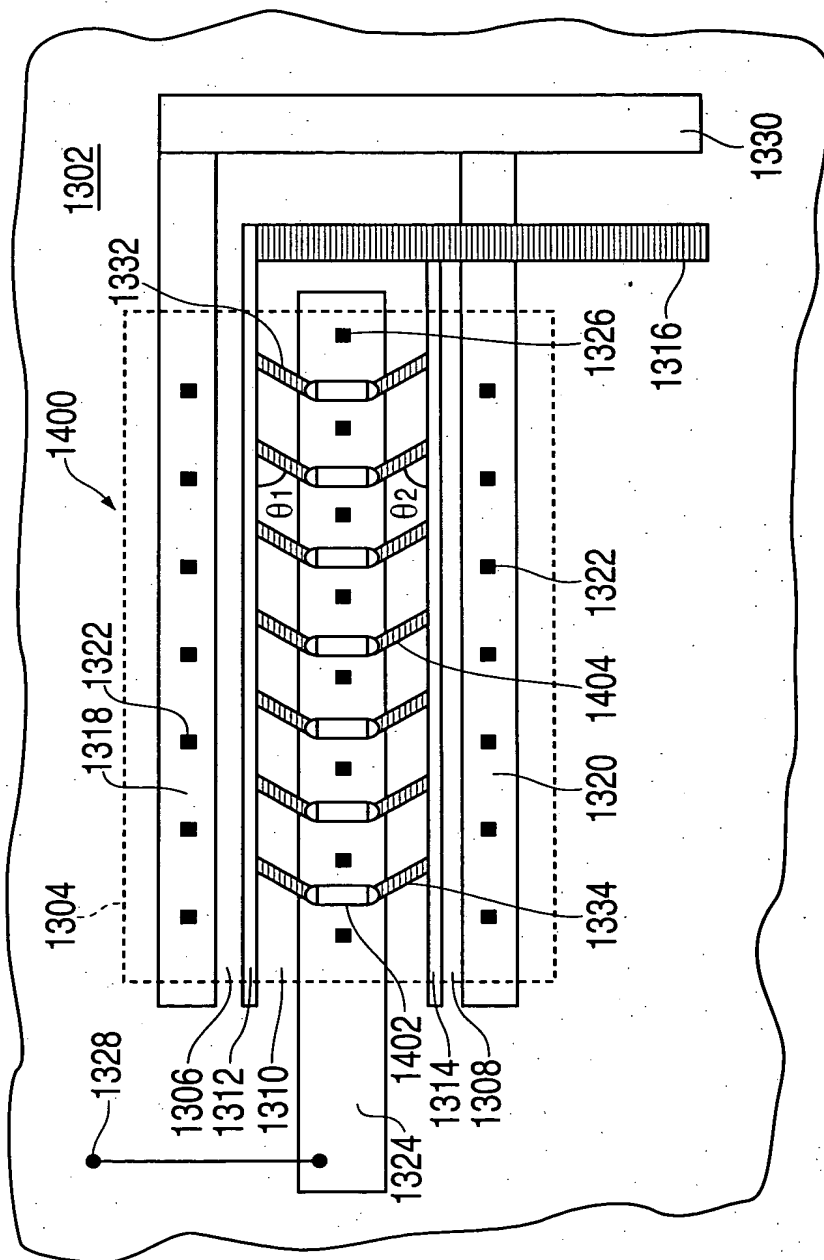
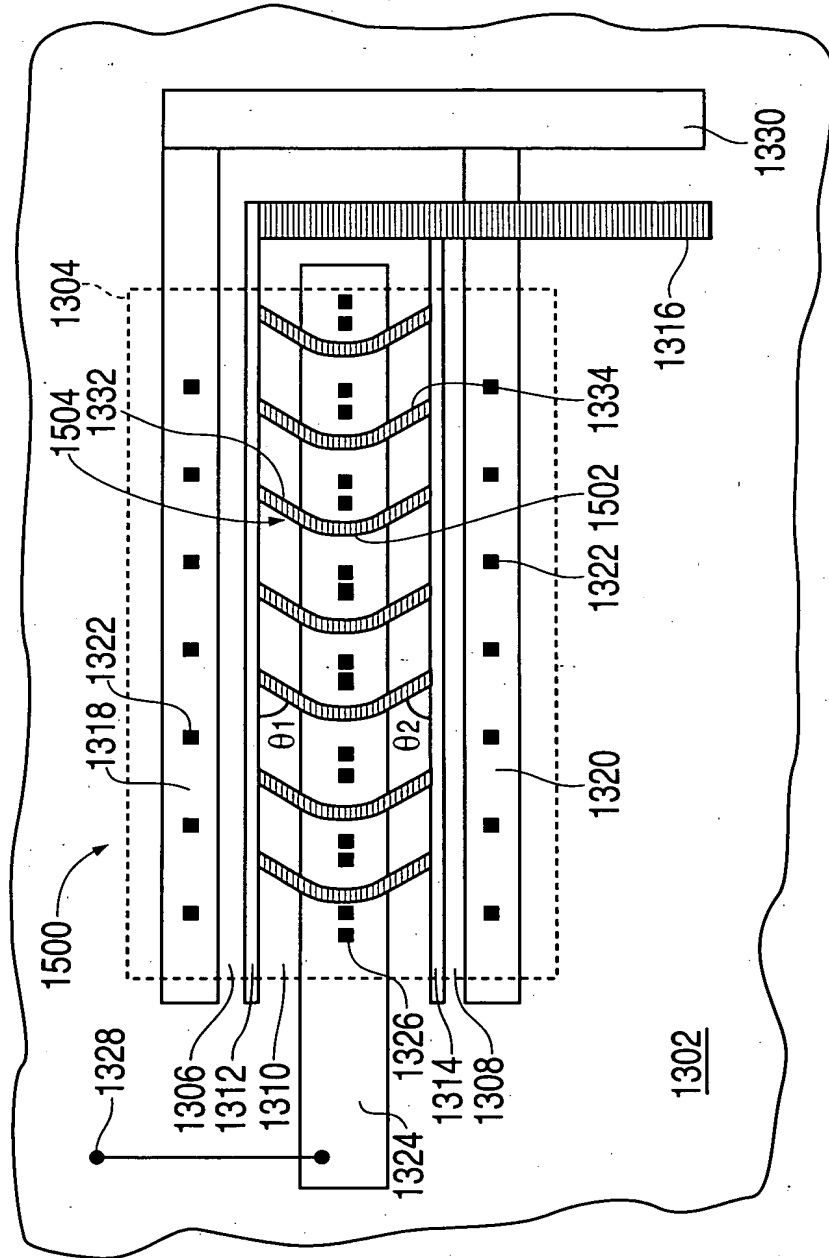


FIG. 15



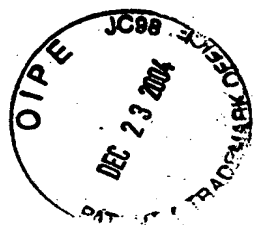


FIG. 16

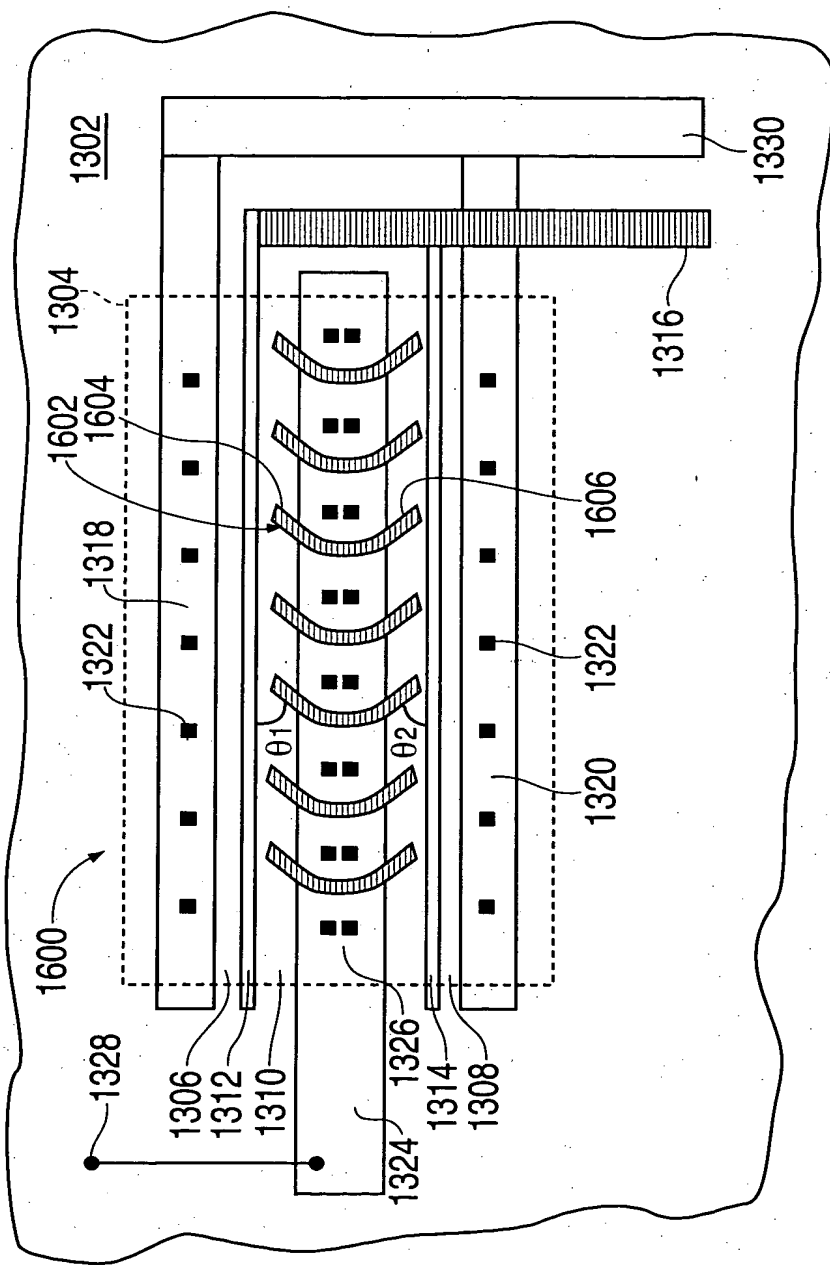
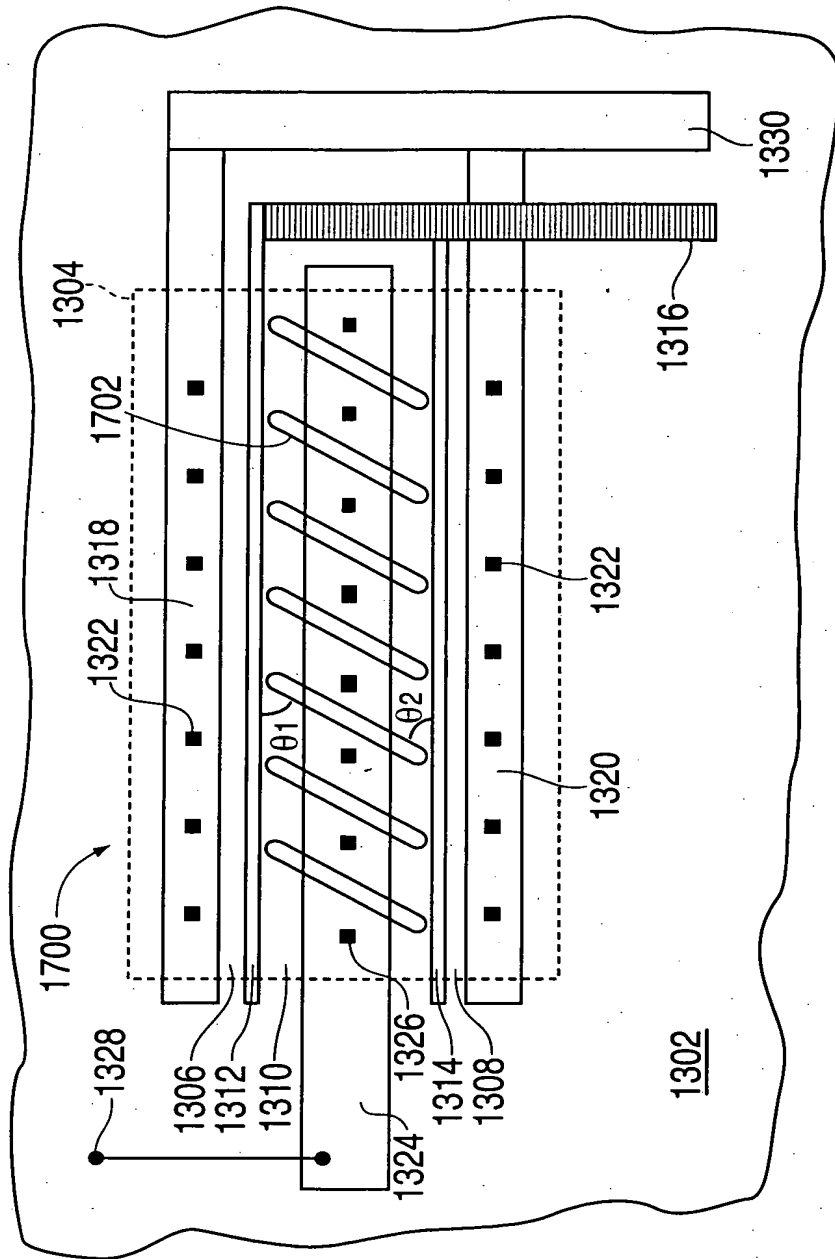


FIG. 17



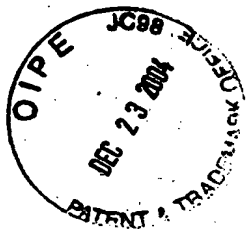
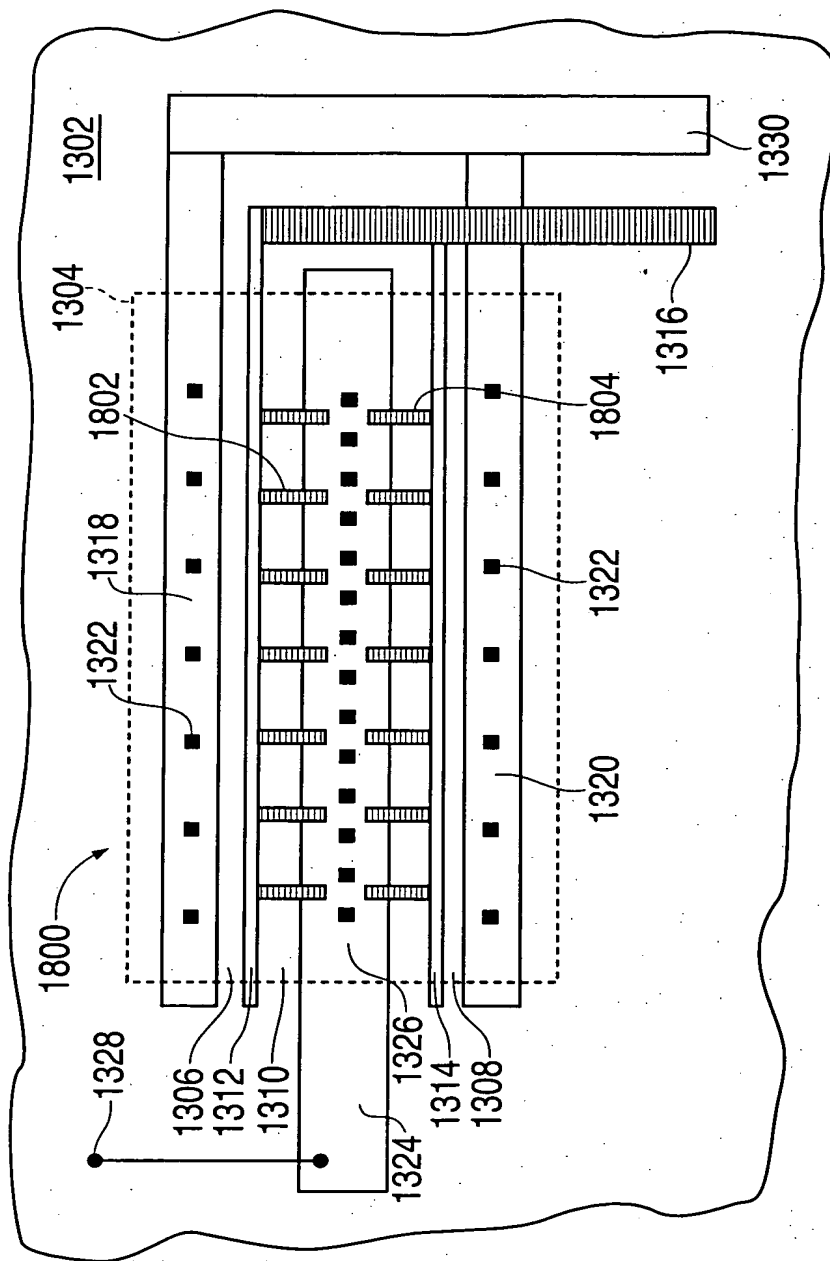


FIG. 18



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FIG. 19

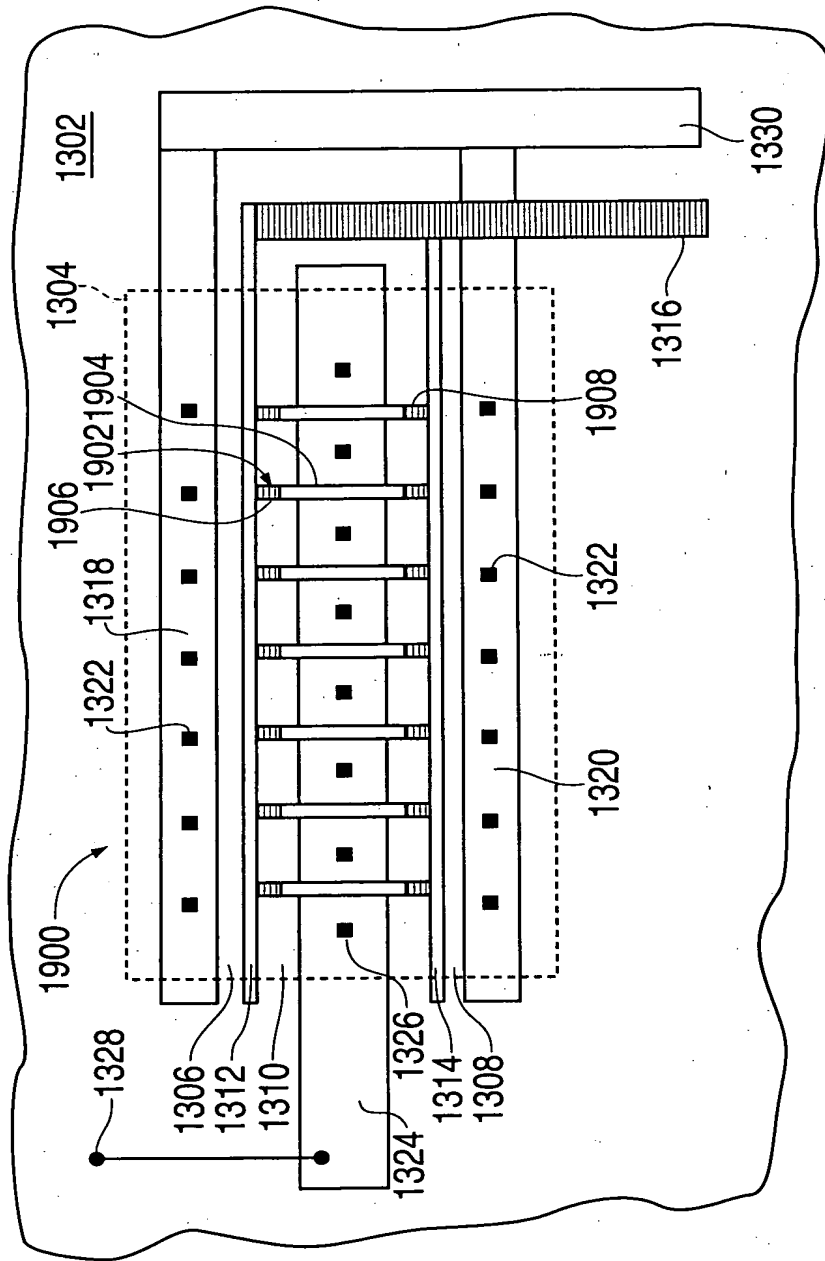




FIG. 20

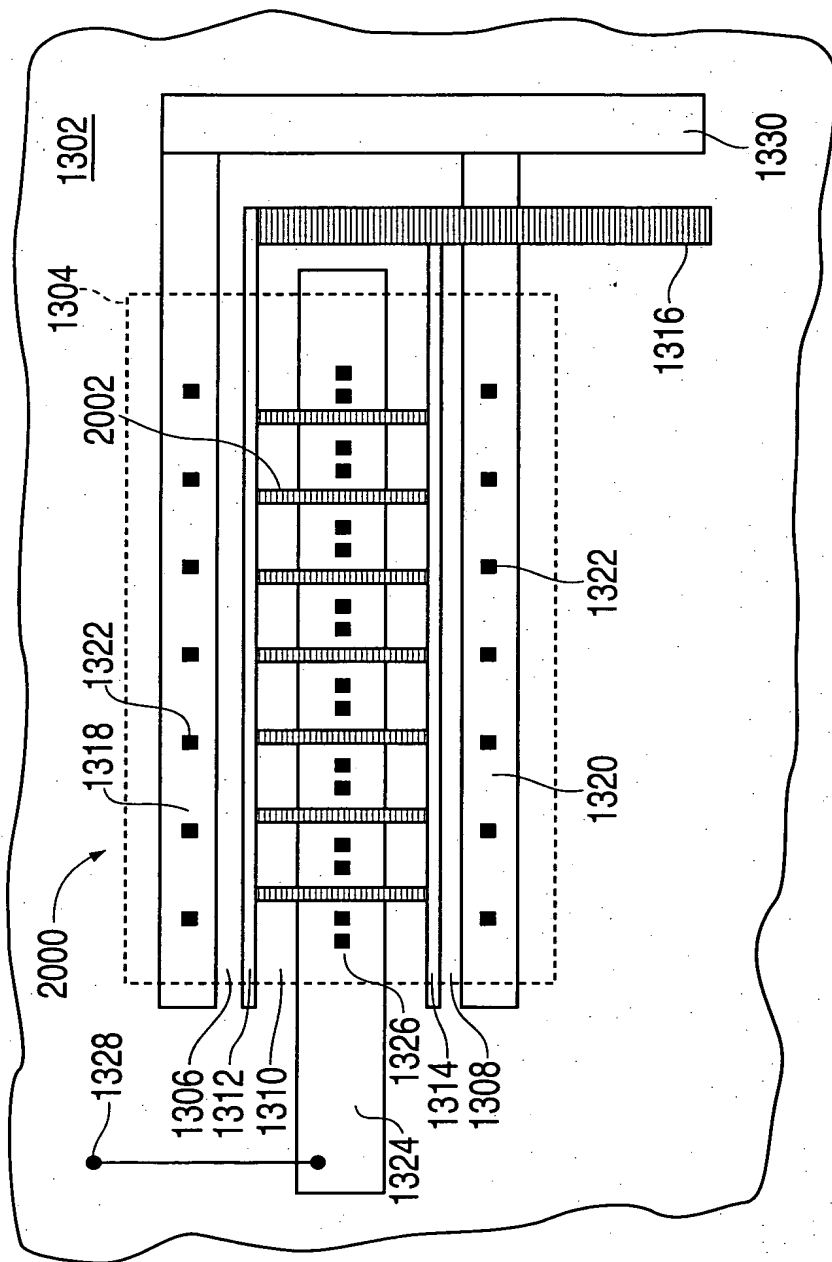
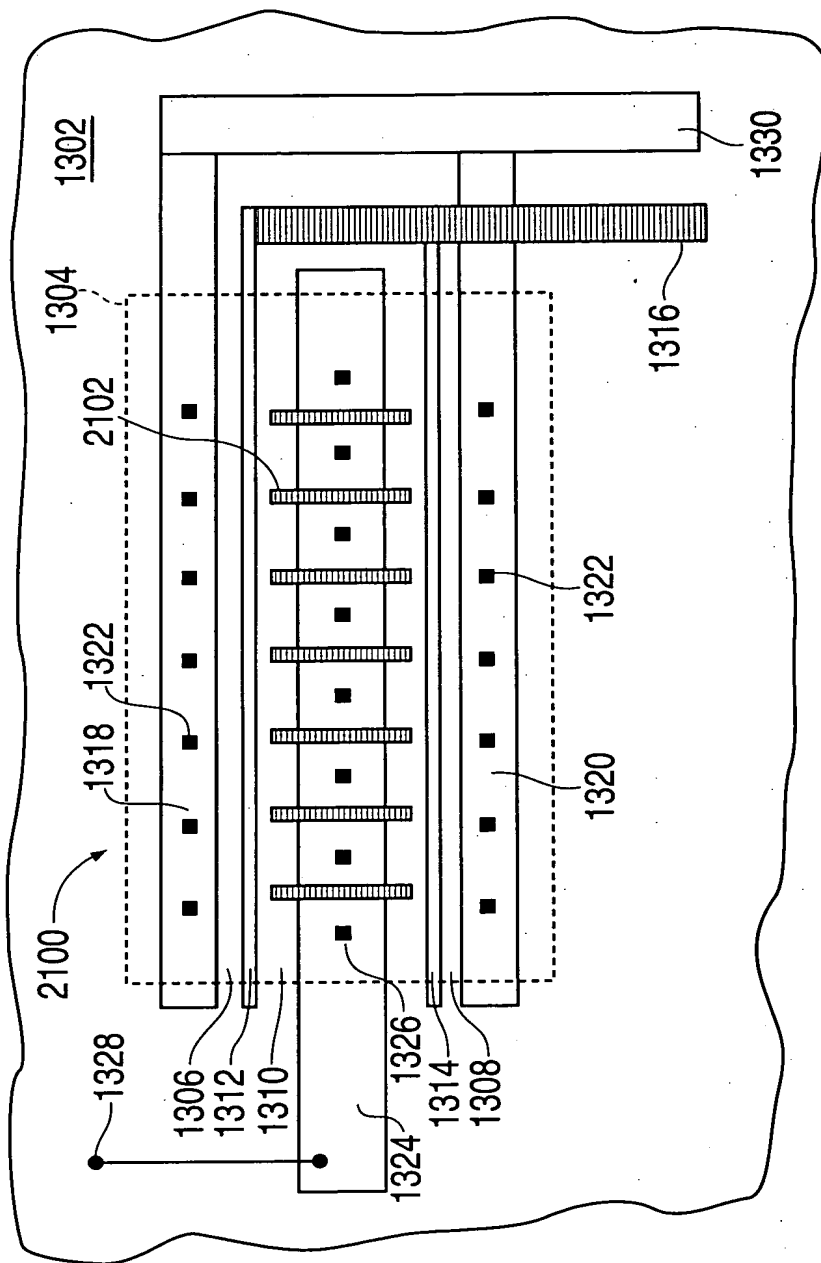




FIG. 21



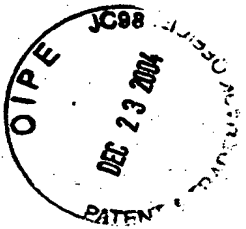


FIG. 22

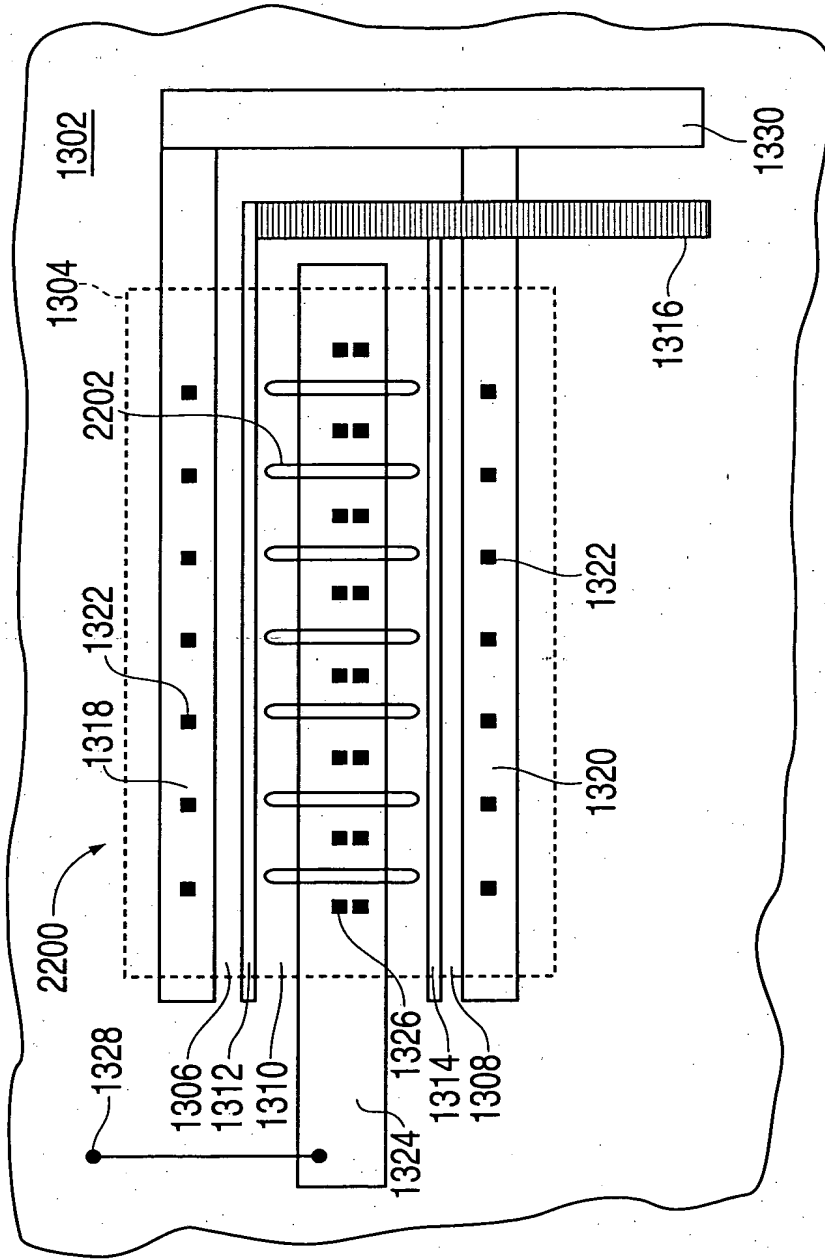




FIG. 23

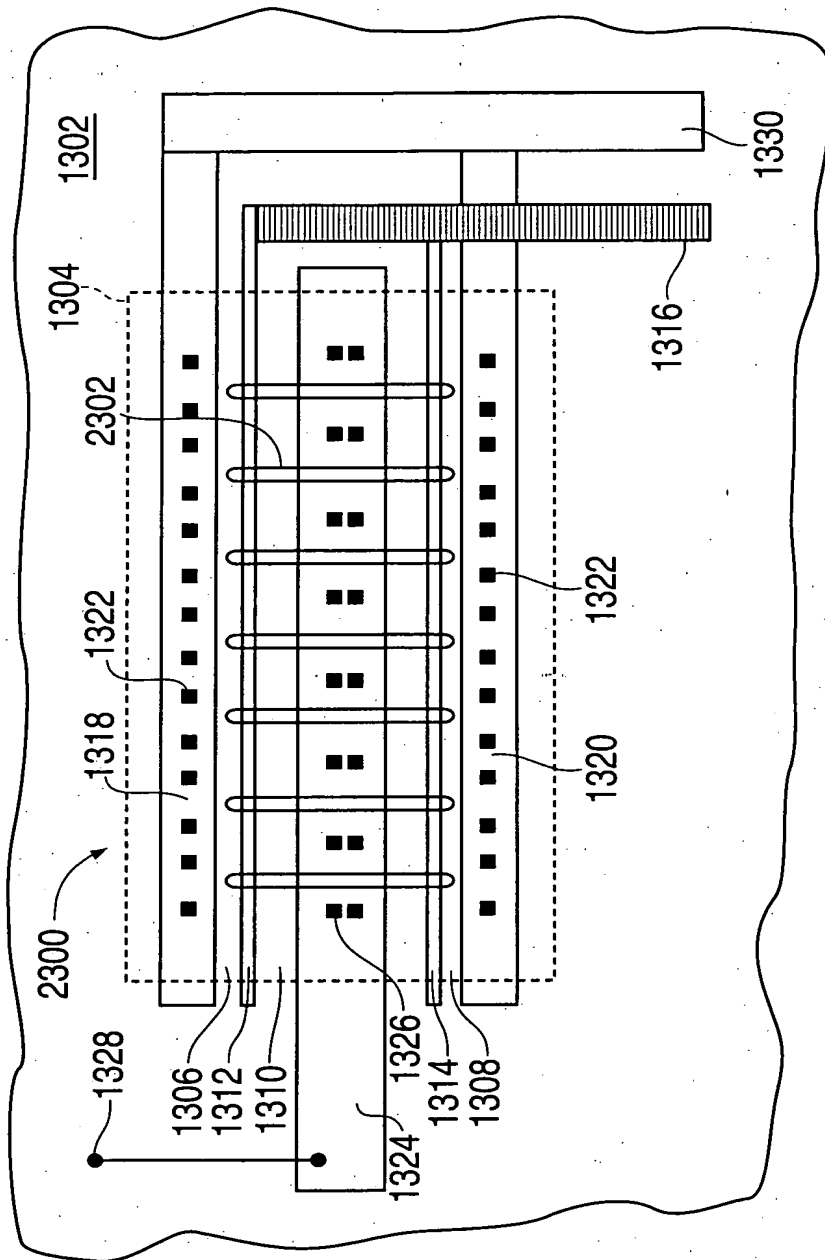


FIG. 24

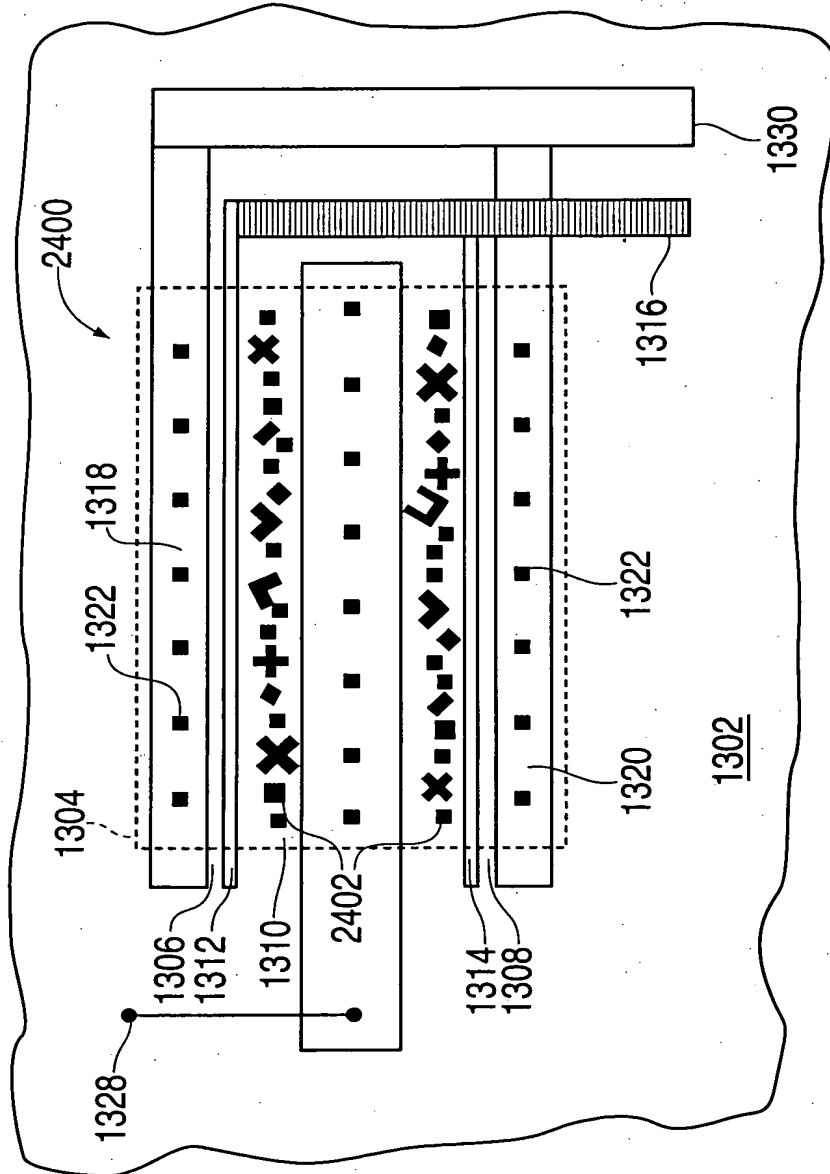




FIG. 26

